STMicroelectronics - STM32F746VGT7 Datasheet

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M7
Core Size	32-Bit Single-Core
Speed	216MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SAI, SD, SPDIF-Rx, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	320K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f746vgt7

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2 Functional overview

2.1 ARM® Cortex®-M7 with FPU

The ARM® Cortex®-M7 with FPU processor is the latest generation of ARM processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and a low-power consumption, while delivering an outstanding computational performance and low interrupt latency.

The Cortex®-M7 processor is a highly efficient high-performance featuring:

– Six-stage dual-issue pipeline
– Dynamic branch prediction
– Harvard caches (4 Kbytes of I-cache and 4 Kbytes of D-cache)
– 64-bit AXI4 interface
– 64-bit ITCM interface
– 2x32-bit DTCM interfaces

The processor supports the following memory interfaces:

- Tightly Coupled Memory (TCM) interface.
- Harvard instruction and data caches and AXI master (AXIM) interface.
- Dedicated low-latency AHB-Lite peripheral (AHBP) interface.

The processor supports a set of DSP instructions which allow efficient signal processing and complex algorithm execution.

Its single precision FPU (floating point unit) speeds up the software development by using metalanguage development tools, while avoiding saturation.

Figure 2 shows the general block diagram of the STM32F745xx and STM32F746xx devices.

Note: Cortex®-M7 with FPU core is binary compatible with the Cortex®-M4 core.

2.2 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

2.22.1 Advanced-control timers (TIM1, TIM8)

The advanced-control timers (TIM1, TIM8) can be seen as three-phase PWM generators multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead times. They can also be considered as complete general-purpose timers. Their 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge- or center-aligned modes)
- One-pulse mode output

If configured as standard 16-bit timers, they have the same features as the general-purpose TIMx timers. If configured as 16-bit PWM generators, they have full modulation capability (0-100%).

The advanced-control timer can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

TIM1 and TIM8 support independent DMA request generation.

2.22.2 General-purpose timers (TIMx)

There are ten synchronizable general-purpose timers embedded in the STM32F74xxx devices (see *Table 6* for differences).

- **TIM2, TIM3, TIM4, TIM5**

  The STM32F74xxx include 4 full-featured general-purpose timers: TIM2, TIM5, TIM3, and TIM4.The TIM2 and TIM5 timers are based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. The TIM3 and TIM4 timers are based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They all feature 4 independent channels for input capture/output compare, PWM or one-pulse mode output. This gives up to 16 input capture/output compare/PWMs on the largest packages.

  The TIM2, TIM3, TIM4, TIM5 general-purpose timers can work together, or with the other general-purpose timers and the advanced-control timers TIM1 and TIM8 via the Timer Link feature for synchronization or event chaining.

  Any of these general-purpose timers can be used to generate PWM outputs.

  TIM2, TIM3, TIM4, TIM5 all have independent DMA request generation. They are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 4 hall-effect sensors.

- **TIM9, TIM10, TIM11, TIM12, TIM13, and TIM14**

  These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler. TIM10, TIM11, TIM13, and TIM14 feature one independent channel, whereas TIM9 and TIM12 have two independent channels for input capture/output compare, PWM or one-pulse mode output. They can be synchronized with the TIM2, TIM3, TIM4, TIM5 full-featured general-purpose timers. They can also be used as simple time bases.

2.23 Inter-integrated circuit interface (I^2C)

The device embeds 4 I2C. Refer to *Table 7: I2C implementation* for the features implementation.

The I^2C bus interface handles communication between the microcontroller and the serial I^2C bus. It controls all I^2C bus-specific sequencing, protocol, arbitration and timing.

The I2C peripheral supports:

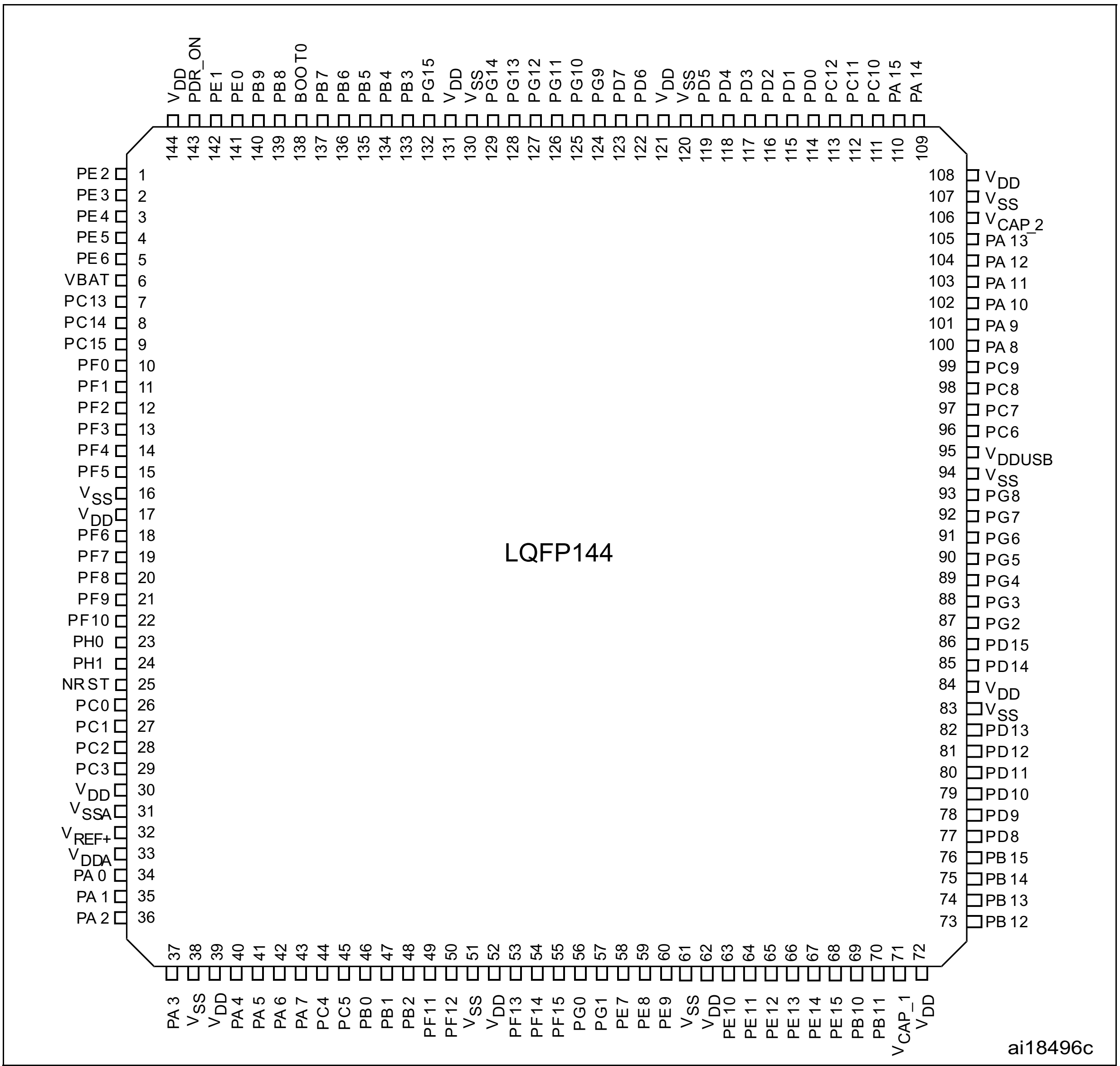
- I^2C-bus specification and user manual rev. 5 compatibility:
  - Slave and master modes, multimaster capability
  - Standard-mode (Sm), with a bitrate up to 100 kbit/s
  - Fast-mode (Fm), with a bitrate up to 400 kbit/s
  - 7-bit and 10-bit addressing mode, multiple 7-bit slave addresses
  - Programmable setup and hold times
  - Optional clock stretching
- System Management Bus (SMBus) specification rev 2.0 compatibility:
  - Hardware PEC (Packet Error Checking) generation and verification with ACK control
  - Address resolution protocol (ARP) support
  - SMBus alert
- Power System Management Protocol (PMBus™) specification rev 1.1 compatibility
- Independent clock: a choice of independent clock sources allowing the I2C communication speed to be independent from the PCLK reprogramming.
- Programmable analog and digital noise filters
- 1-byte buffer with DMA capability

Table 7. I2C implementation

I2C features(1)	I2C1	I2C2	I2C3	I2C4
Standard-mode (up to 100 kbit/s)	X	X	X	X
Fast-mode (up to 400 kbit/s)	X	X	X	X
Programmable analog and digital noise filters	X	X	X	X
SMBus/PMBus hardware support	X	X	X	X
Independent clock	X	X	X	X

1. X: supported

Figure 14. STM32F74xZx LQFP144 pinout



1. The above figure shows the package top view.

Table 10. STM32F745xx and STM32F746xx pin and ball definition (continued)

Pin Number								Pin name (function after reset)[1]	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	TFBGA100	WLCSP143	LQFP144	UFBGA176	LQFP176	LQFP208	TFBGA216						
-	-	-	-	G4	44	47	J4	PH3	I/O	FT	-	QUADSPI_BK2_IO1, SAI2_MCK_B, ETH_MII_COL, FMC_SDNE0, LCD_R1, EVENTOUT	-
-	-	-	-	H4	45	48	H4	PH4	I/O	FT	-	I2C2_SCL, OTG_HS_ULPI_NXT, EVENTOUT	-
-	-	-	-	J4	46	49	J3	PH5	I/O	FT	-	I2C2_SDA, SPI5_NSS, FMC_SDNWE, EVENTOUT	-
25	K2	M11	37	R2	47	50	R2	PA3	I/O	FT	(4)	TIM2_CH4, TIM5_CH4, TIM9_CH2, USART2_RX, OTG_HS_ULPI_D0, ETH_MII_COL, LCD_B5, EVENTOUT	ADC123_IN3
26	J1	-	38	-	-	51	K6	VSS	S	-	-	-	-
-	E6	N11	-	L4	48	-	L5	BYPASS_REG	I	FT	-	-	-
27	K1	J8	39	K4	49	52	K5	VDD	S	-	-	-	-
28	G3	M10	40	N4	50	53	N4	PA4	I/O	TTa	(4)	SPI1_NSS/I2S1_WS, SPI3_NSS/I2S3_WS, USART2_CK, OTG_HS_SOF, DCMI_HSYNC, LCD_VSYNC, EVENTOUT	ADC12_IN4, DAC_OUT1
29	H3	M9	41	P4	51	54	P4	PA5	I/O	TTa	(4)	TIM2_CH1/TIM2_ETR, TIM8_CH1N, SPI1_SCK/I2S1_CK, OTG_HS_ULPI_CK, LCD_R4, EVENTOUT	ADC12_IN5, DAC_OUT2
30	J3	N10	42	P3	52	55	P3	PA6	I/O	FT	(4)	TIM1_BKIN, TIM3_CH1, TIM8_BKIN, SPI1_MISO, TIM13_CH1, DCMI_PIXCLK, LCD_G2, EVENTOUT	ADC12_IN6

Table 10. STM32F745xx and STM32F746xx pin and ball definition (continued)

Pin Number								Pin name (function after reset)(1)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	TFBGA100	WLCSP143	LQFP144	UFBGA176	LQFP176	LQFP208	TFBGA216						
-	-	-	-	N12	84	97	N13	PH7	I/O	FT	-	I2C3_SCL, SPI5_MISO, ETH_MII_RXD3, FMC_SDCKE1, DCMI_D9, EVENTOUT	-
-	-	-	-	M12	85	98	P14	PH8	I/O	FT	-	I2C3_SDA, FMC_D16, DCMI_HSYNC, LCD_R2, EVENTOUT	-
-	-	-	-	M13	86	99	N14	PH9	I/O	FT	-	I2C3_SMBA, TIM12_CH2, FMC_D17, DCMI_D0, LCD_R3, EVENTOUT	-
-	-	-	-	L13	87	100	P15	PH10	I/O	FT	-	TIM5_CH1, I2C4_SMBA, FMC_D18, DCMI_D1, LCD_R4, EVENTOUT	-
-	-	-	-	L12	88	101	N15	PH11	I/O	FT	-	TIM5_CH2, I2C4_SCL, FMC_D19, DCMI_D2, LCD_R5, EVENTOUT	-
-	-	-	-	K12	89	102	M15	PH12	I/O	FT	-	TIM5_CH3, I2C4_SDA, FMC_D20, DCMI_D3, LCD_R6, EVENTOUT	-
-	-	-	-	H12	90	-	K10	VSS	S	-	-	-	-
-	-	-	-	J12	91	103	K11	VDD	S	-	-	-	-
51	K8	M2	73	P12	92	104	L13	PB12	I/O	FT	-	TIM1_BKIN, I2C2_SMBA, SPI2_NSS/I2S2_WS, USART3_CK, CAN2_RX, OTG_HS_ULPI_D5, ETH_MII_TXD0/ETH_RMII_TXD0, OTG_HS_ID, EVENTOUT	-
52	J8	N1	74	P13	93	105	K14	PB13	I/O	FT	-	TIM1_CH1N, SPI2_SCK/I2S2_CK, USART3_CTS, CAN2_TX, OTG_HS_ULPI_D6, ETH_MII_TXD1/ETH_RMII_TXD1, EVENTOUT	OTG_HS_VBUS

Table 10. STM32F745xx and STM32F746xx pin and ball definition (continued)

Pin Number								Pin name (function after reset)(1)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	TFBGA100	WLCSP143	LQFP144	UFBGA176	LQFP176	LQFP208	TFBGA216						
53	H10	K3	75	R14	94	106	R14	PB14	I/O	FT	-	TIM1_CH2N, TIM8_CH2N, SPI2_MISO, USART3_RTS, TIM12_CH1, OTG_HS_DM, EVENTOUT	-
54	G10	J3	76	R15	95	107	R15	PB15	I/O	FT	-	RTC_REFIN, TIM1_CH3N, TIM8_CH3N, SPI2_MOSI/I2S2_SD, TIM12_CH2, OTG_HS_DP, EVENTOUT	-
55	K9	L2	77	P15	96	108	L15	PD8	I/O	FT	-	USART3_TX, SPDIFRX_IN11, FMC_D13, EVENTOUT	-
56	J9	M1	78	P14	97	109	L14	PD9	I/O	FT	-	USART3_RX, FMC_D14, EVENTOUT	-
57	H9	H4	79	N15	98	110	K15	PD10	I/O	FT	-	USART3_CK, FMC_D15, LCD_B3, EVENTOUT	-
58	G9	K2	80	N14	99	111	N10	PD11	I/O	FT	-	I2C4_SMBA, USART3_CTS, QUADSPI_BK1_IO0, SAI2_SD_A, FMC_A16/FMC_CLE, EVENTOUT	-
59	K10	H6	81	N13	100	112	M10	PD12	I/O	FT	-	TIM4_CH1, LPTIM1_IN1, I2C4_SCL, USART3_RTS, QUADSPI_BK1_IO1, SAI2_FS_A, FMC_A17/FMC_ALE, EVENTOUT	-
60	J10	H5	82	M15	101	113	M11	PD13	I/O	FT	-	TIM4_CH2, LPTIM1_OUT, I2C4_SDA, QUADSPI_BK1_IO3, SAI2_SCK_A, FMC_A18, EVENTOUT	-

pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

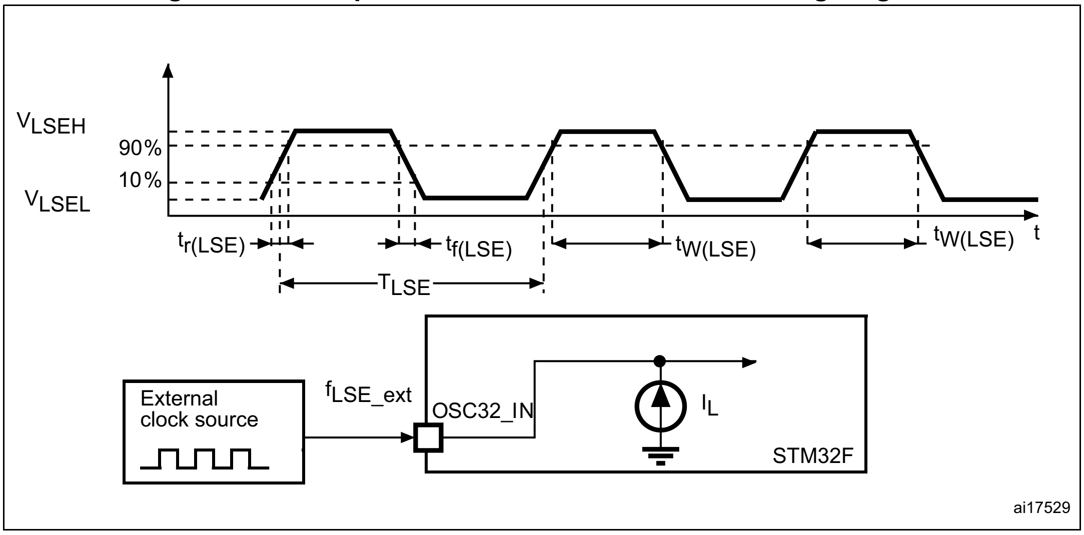
C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT}$

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

Table 34. Switching output I/O current consumption(1)

Symbol	Parameter	Conditions	I/O toggling frequency (fsw) MHz	Typ V_{DD} = 3.3 V	Typ V_{DD} = 1.8 V	Unit
I_{DDIO}	I/O switching Current	C_{EXT} = 0 pF $C = C_{INT} + C_S + C_{EXT}$	2	0.1	0.1	mA
			8	0.4	0.2	
			25	1.1	0.7	
			50	2.4	1.3	
			60	3.1	1.6	
			84	4.3	2.4	
			90	4.9	2.6	
			100	5.4	2.8	
			108	5.6	-	
		C_{EXT} = 10 pF $C = C_{INT} + C_S + C_{EXT}$	2	0.2	0.1	
			8	0.6	0.3	
			25	1.8	1.1	
			50	3.1	2.3	
			60	4.6	3.4	
			84	9.7	3.6	
			90	10.12	5.2	
			100	14.92	5.4	
			108	18.11	-	

Figure 31. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 26 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 39*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 39. HSE 4-26 MHz oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	4	-	26	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
I_{DD}	HSE current consumption	V_{DD}=3.3 V, ESR= 30 Ω, C_L=5 pF@25 MHz	-	450	-	µA
		V_{DD}=3.3 V, ESR= 30 Ω, C_L=10 pF@25 MHz	-	530	-	
ACC_{HSE}(2)	HSE accuracy	-	− 500	-	500	ppm
G_{m}_crit_max	Maximum critical crystal g_m	Startup	-	-	1	mA/V
$t_{SU(HSE)}$(3)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Guaranteed by design.
2. This parameter depends on the crystal used in the application. The minimum and maximum values must be respected to comply with USB standard specifications.
3. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is based on characterization results. It is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Table 50. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min[1]	
N_{END}	Endurance	T_A = –40 to +85 °C (6 suffix versions) T_A = –40 to +105 °C (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle[2] at T_A = 85 °C	30	Years
		1 kcycle[2] at T_A = 105 °C	10	
		10 kcycles[2] at T_A = 55 °C	20	

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

5.3.14 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 51*. They are based on the EMS levels and classes defined in application note AN1709.

Table 51. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP176, T_A = +25 °C, f_{HCLK} = 216 MHz, conforms to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, TFBGA216, T_A =+25 °C, f_{HCLK} = 216 MHz, conforms to IEC 61000-4-2	4A

As a consequence, it is recommended to add a serial resistor (1 kΩ) located as close as possible to the MCU to the pins exposed to noise (connected to tracks longer than 50 mm on PCB).

Refer to *Section 5.3.17: I/O port characteristics* for more details on the input/output alternate function characteristics (CK, SD, WS).

Table 77. I^2S dynamic characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I2S Main clock output	-	256x8K	256xFs(2)	MHz
f_{CK}	I2S clock frequency	Master data: 32 bits	-	64xFs	MHz
		Slave data: 32 bits	-	64xFs	
D_{CK}	I2S clock frequency duty cycle	Slave receiver	30	70	%
$t_{v(WS)}$	WS valid time	Master mode	-	5	ns
$t_{h(WS)}$	WS hold time	Master mode	0	-	
$t_{su(WS)}$	WS setup time	Slave mode	5	-	ns
		Slave mode PCM short pulse mode(3)	3	-	
$t_{h(WS)}$	WS hold time	Slave mode	0	-	
		Slave mode PCM short pulse mode(3)	2	-	
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	5	-	
$t_{su(SD\_SR)}$		Slave receiver	1	-	
$t_{h(SD\_MR)}$	Data input hold time	Master receiver	5	-	
$t_{h(SD\_SR)}$		Slave receiver	1.5	-	
$t_{v(SD\_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	16	
$t_{v(SD\_MT)}$		Master transmitter (after enable edge)	-	3.5	
$t_{h(SD\_ST)}$	Data output hold time	Slave transmitter (after enable edge)	5	-	
$t_{h(SD\_MT)}$		Master transmitter (after enable edge)	0	-	

1. Guaranteed by characterization results.
2. The maximum value of 256xFs is 45 MHz (APB1 maximum frequency).
3. Measurement done with respect to I2S_CK rising edge.

Note: Refer to RM0385 reference manual I2S section for more details on the sampling frequency (F_S).

*f_{MCK}, f_{CK}, and D_{CK} values reflect only the digital peripheral behavior. The values of these parameters might be slightly impacted by the source clock precision. D_{CK} depends mainly on the value of ODD bit. The digital contribution leads to a minimum value of (I2SDIV/(2*I2SDIV+ODD) and a maximum value of (I2SDIV+ODD)/(2*I2SDIV+ODD). F_S maximum value is supported for each mode/condition.*

Figure 61. Asynchronous multiplexed PSRAM/NOR write waveforms

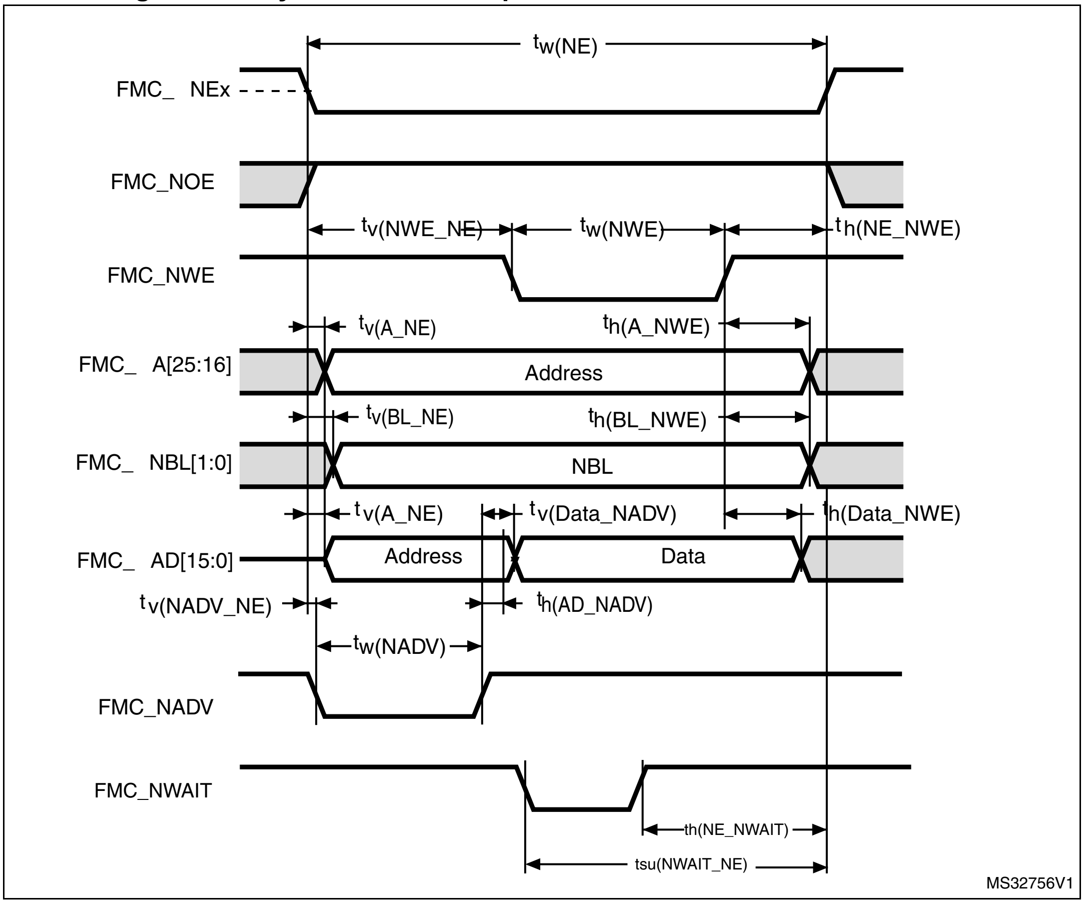


Table 94. Asynchronous multiplexed PSRAM/NOR write timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$4T_{HCLK}-0.5$	$4T_{HCLK}+1.5$	ns
$t_{v(NWE\_NE)}$	FMC_NEx low to FMC_NWE low	$T_{HCLK}-1$	$T_{HCLK}+0.5$	
$t_{w(NWE)}$	FMC_NWE low time	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	
$t_{h(NE\_NWE)}$	FMC_NWE high to FMC_NE high hold time	T_{HCLK}	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	0	0.5	
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK}-0.5$	$T_{HCLK}+1.5$	
$t_{h(AD\_NADV)}$	FMC_AD(adress) valid hold time after FMC_NADV high)	$T_{HCLK}-2$	-	
$t_{h(A\_NWE)}$	Address hold time after FMC_NWE high	T_{HCLK}	-	
$t_{h(BL\_NWE)}$	FMC_BL hold time after FMC_NWE high	$T_{HCLK}-2$	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	0	
$t_{v(Data\_NADV)}$	FMC_NADV high to Data valid	-	$T_{HCLK}+2$	
$t_{h(Data\_NWE)}$	Data hold time after FMC_NWE high	$T_{HCLK}+0.5$	-	

Figure 66. NAND controller waveforms for read access

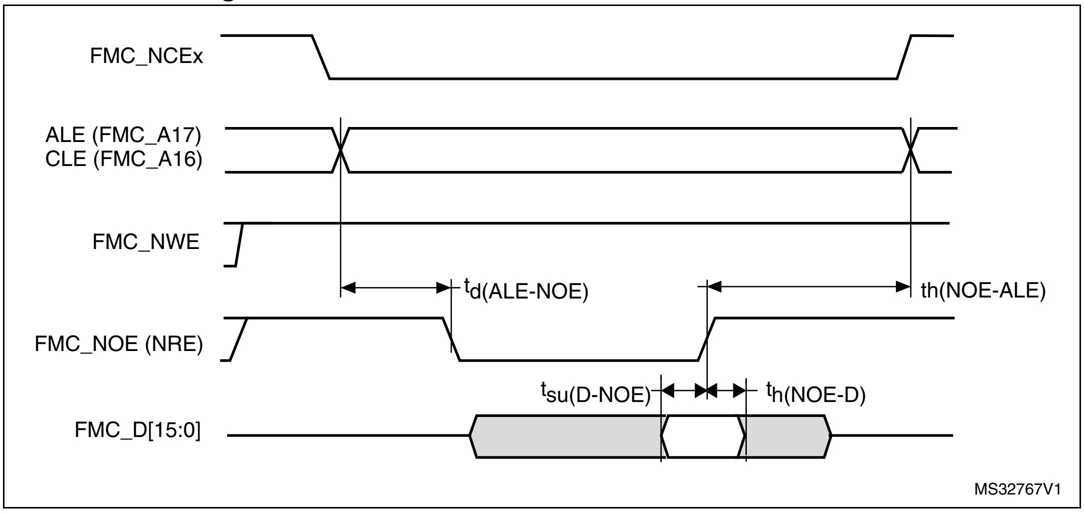


Figure 67. NAND controller waveforms for write access

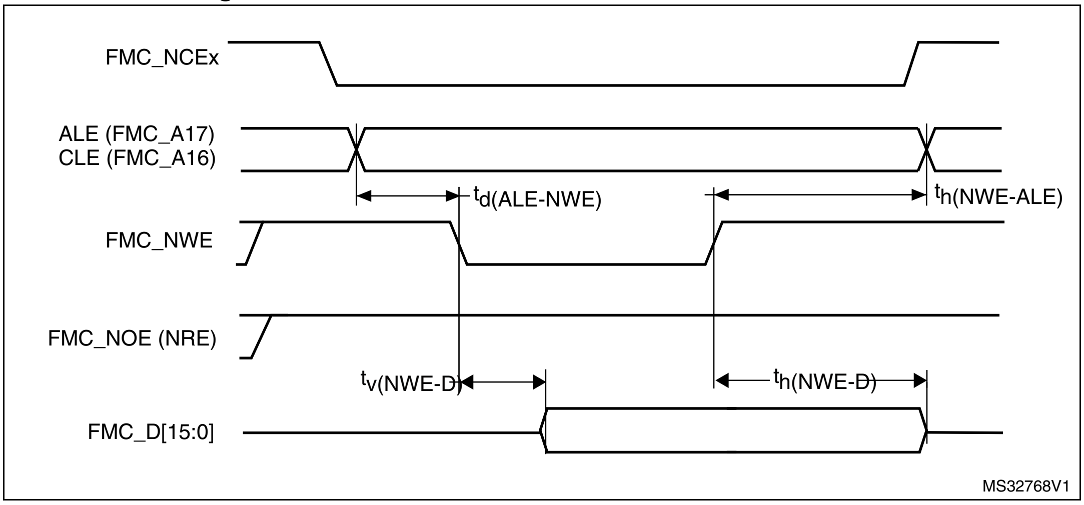


Figure 68. NAND controller waveforms for common memory read access

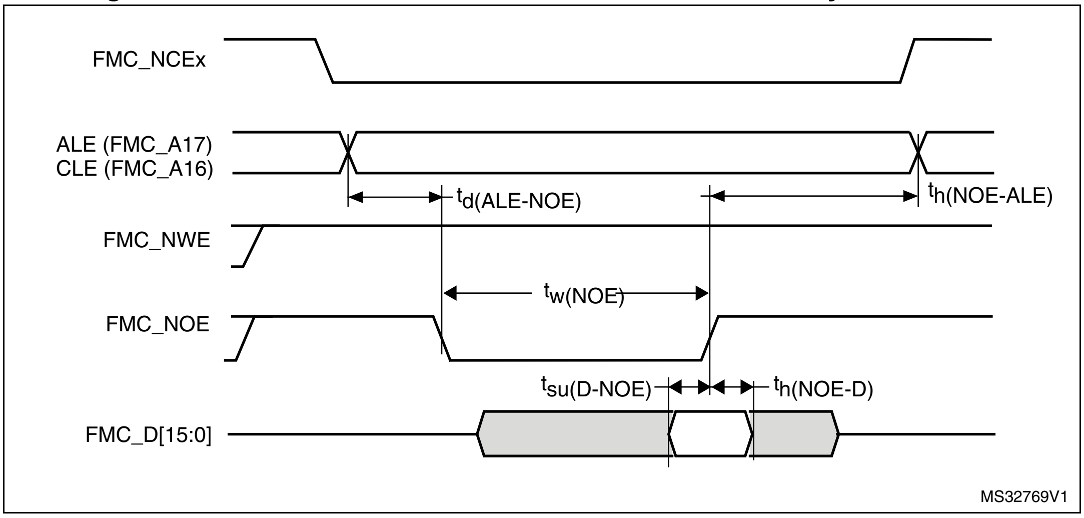


Table 102. SDRAM read timings[1]

Symbol	Parameter	Min	Max	Unit
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	ns
$t_{su(SDCLKH\_Data)}$	Data input setup time	3.5	-	
$t_{h(SDCLKH\_Data)}$	Data input hold time	1.5	-	
$t_{d(SDCLKL\_Add)}$	Address valid time	-	4	
$t_{d(SDCLKL- SDNE)}$	Chip select valid time	-	0.5	
$t_{h(SDCLKL\_SDNE)}$	Chip select hold time	0	-	
$t_{d(SDCLKL\_SDNRAS)}$	SDNRAS valid time	-	0.5	
$t_{h(SDCLKL\_SDNRAS)}$	SDNRAS hold time	0	-	
$t_{d(SDCLKL\_SDNCAS)}$	SDNCAS valid time	-	0.5	
$t_{h(SDCLKL\_SDNCAS)}$	SDNCAS hold time	0	-	

1. Guaranteed by characterization results.

Table 103. LPSDR SDRAM read timings[1]

Symbol	Parameter	Min	Max	Unit
$t_{W(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	ns
$t_{su(SDCLKH\_Data)}$	Data input setup time	3	-	
$t_{h(SDCLKH\_Data)}$	Data input hold time	1.5	-	
$t_{d(SDCLKL\_Add)}$	Address valid time	-	3.5	
$t_{d(SDCLKL\_SDNE)}$	Chip select valid time	-	0.5	
$t_{h(SDCLKL\_SDNE)}$	Chip select hold time	0	-	
$t_{d(SDCLKL\_SDNRAS}$	SDNRAS valid time	-	0.5	
$t_{h(SDCLKL\_SDNRAS)}$	SDNRAS hold time	0	-	
$t_{d(SDCLKL\_SDNCAS)}$	SDNCAS valid time	-	0.5	
$t_{h(SDCLKL\_SDNCAS)}$	SDNCAS hold time	0	-	

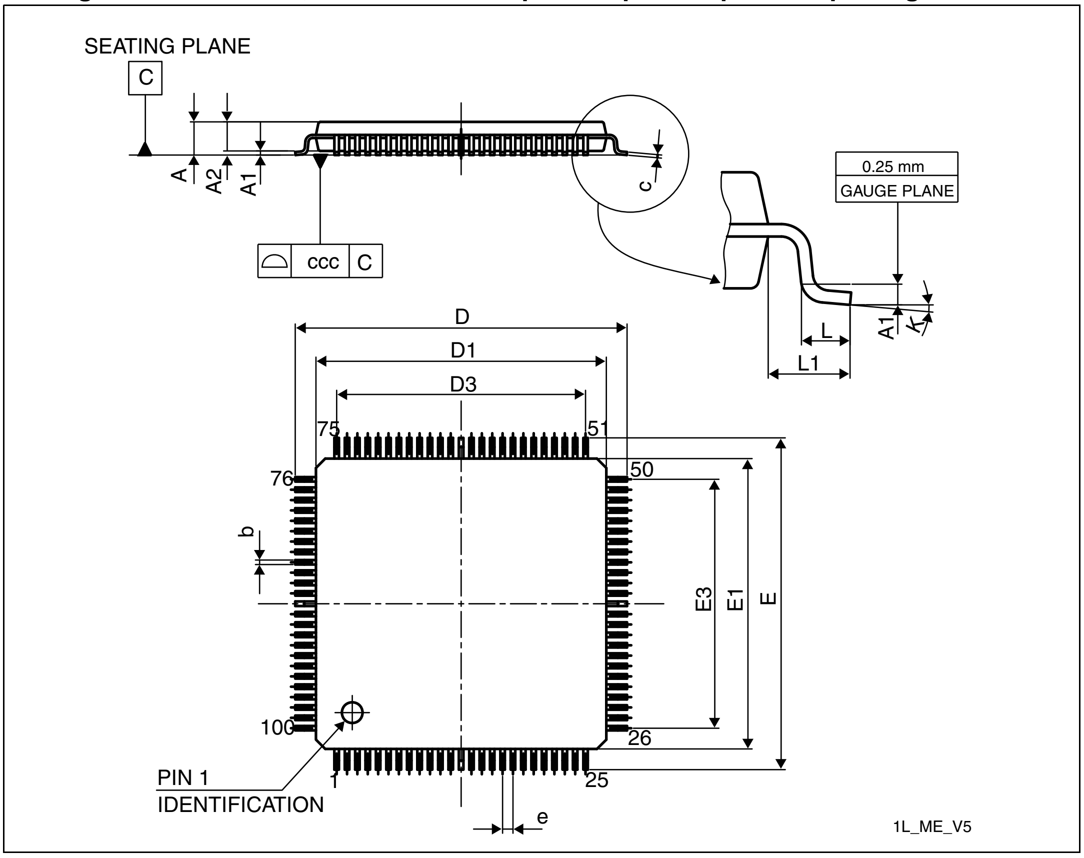
1. Guaranteed by characterization results.

6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

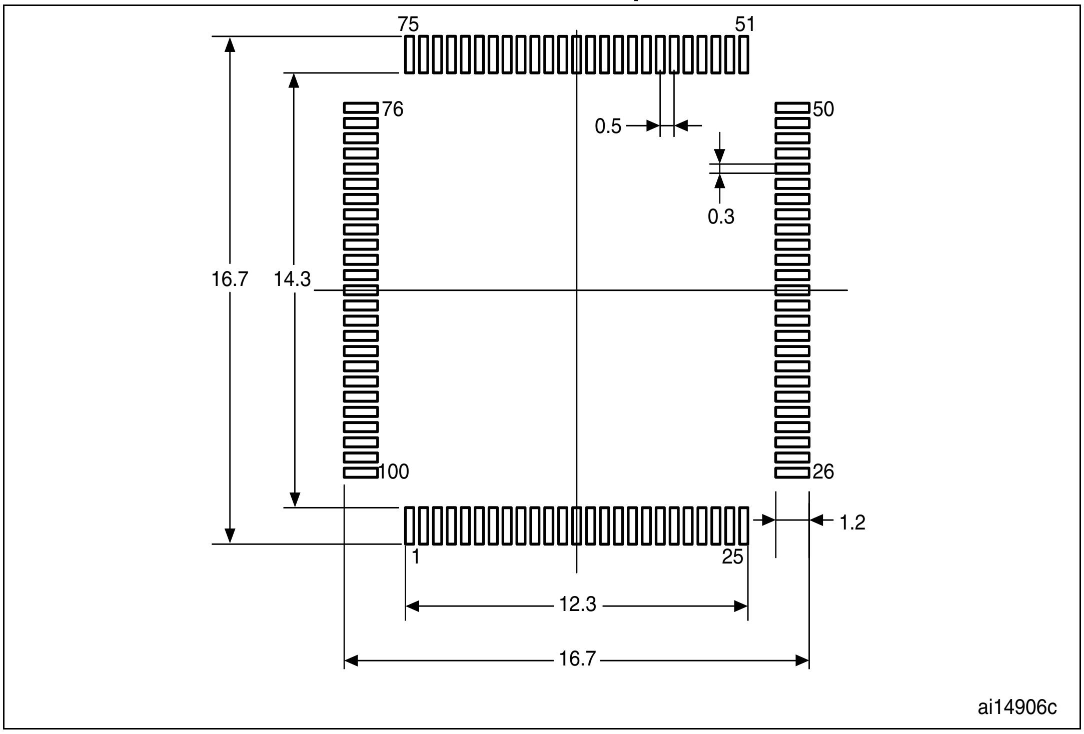
6.1 LQFP100, 14 x 14 mm low-profile quad flat package information

Figure 79. LQFP100, 14 x 14 mm 100-pin low-profile quad flat package outline



1. Drawing is not to scale.

Figure 80. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package recommended footprint

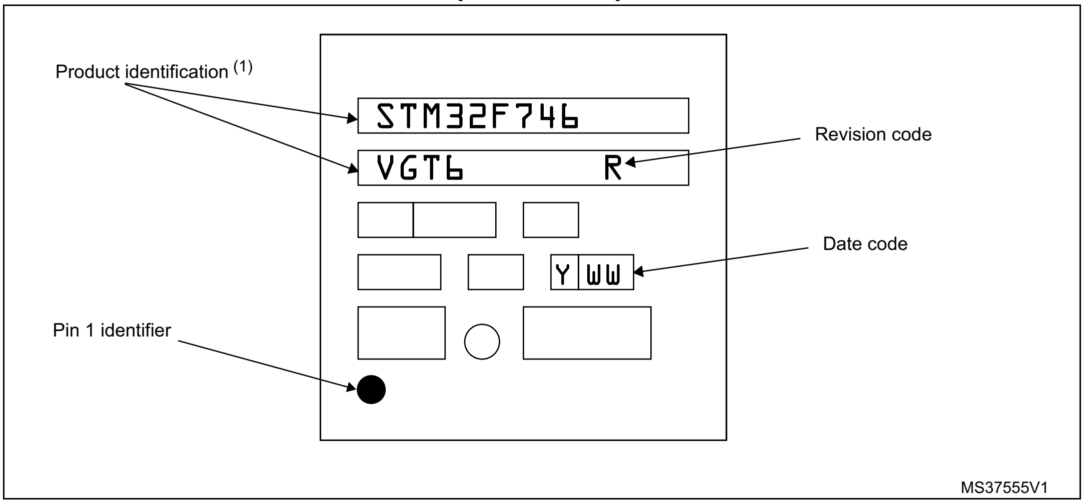


1. Dimensions are expressed in millimeters.

Marking of engineering samples

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 81. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package top view example



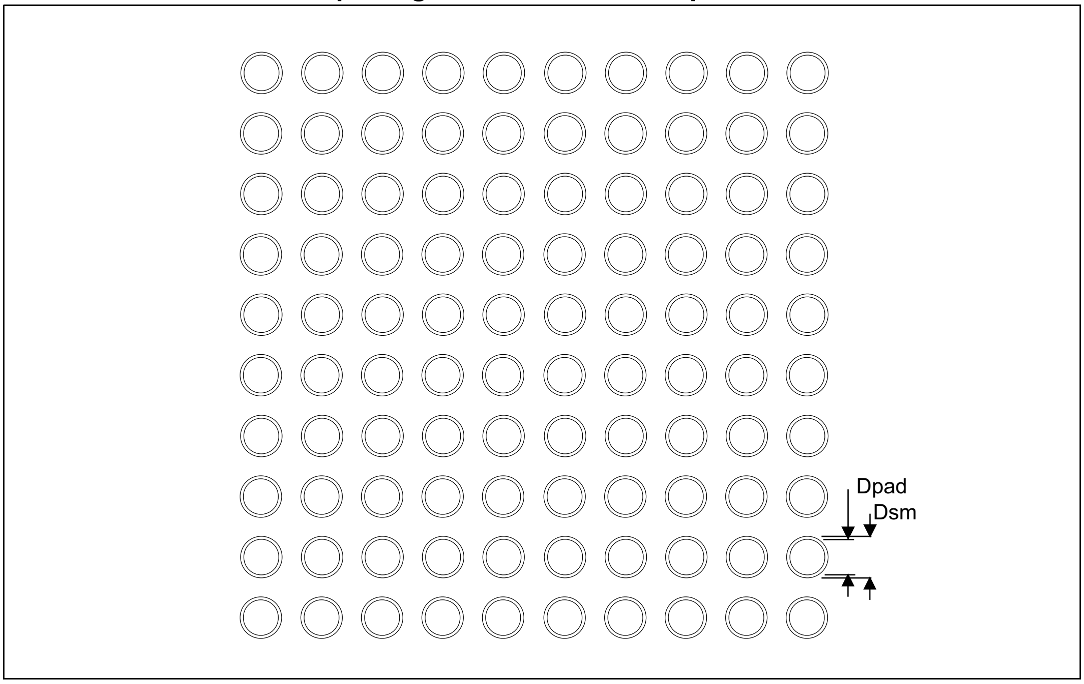
1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Table 113. TFBGA100, 8 x 8 × 0.8 mm thin fine-pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches[(1)]		
	Min	Typ	Max	Min	Typ	Max
D	7.850	8.000	8.150	0.3091	0.3150	0.3209
D1	-	7.200		-	0.2835	-
E	7.850	8.000	8.150	0.3091	0.3150	0.3209
E1	-	7.200	-	-	0.2835	-
e	-	0.800	-	-	0.0315	-
F	-	0.400	-	-	0.0157	-
G	-	0.400	-	-	0.0157	-
ddd	-	-	0.100	-	-	0.0039
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 83. TFBGA100, 8 x 8 x 0.8 mm thin fine-pitch ball grid array package recommended footprint



1. Dimensions are expressed in millimeters.

Appendix A Recommendations when using internal reset OFF

When the internal reset is OFF, the following integrated features are no longer supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled.
- The brownout reset (BOR) circuitry must be disabled.
- The embedded programmable voltage detector (PVD) is disabled.
- V_{BAT} functionality is no more available and VBAT pin should be connected to V_{DD}.
- The over-drive mode is not supported.

A.1 Operating conditions

Table 126. Limitations depending on the operating power supply range

Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait states ($f_{Flashmax}$)	Maximum Flash memory access frequency with wait states (1)(2)	I/O operation	Possible Flash memory operations
V_{DD} =1.7 to 2.1 V(3)	Conversion time up to 1.2 Msps	20 MHz	180 MHz with 8 wait states and over-drive OFF	– No I/O compensation	8-bit erase and program operations only

1. Applicable only when the code is executed from Flash memory. When the code is executed from RAM, no wait state is required.
2. Thanks to the ART accelerator on ITCM interface and L1-cache on AXI interface, the number of wait states given here does not impact the execution speed from the Flash memory since the ART accelerator or L1-cache allows to achieve a performance equivalent to 0-wait state program execution.
3. V_{DD}/V_{DDA} minimum value of 1.7 V, with the use of an external power supply supervisor (refer to *Section 2.17.1: Internal reset ON*).